



M41T56C64

512 bit (64 bit x8) Serial Access TIMEKEEPER[®] SRAM + 64 Kbit (8192 bit x8) EEPROM

PRELIMINARY DATA

FEATURES SUMMARY

- 5V \pm 10% SUPPLY VOLTAGE
- I²C BUS COMPATIBLE
- OPERATING TEMPERATURE OF -40 TO 85°C
- PACKAGING INCLUDES:
 - 18-lead SOIC (with Embedded Crystal)

Serial RTC Features

- COUNTERS FOR SECONDS, MINUTES, HOURS, DAY, DATE, MONTH, YEARS, AND CENTURY
- EMBEDDED CRYSTAL PACKAGE
- SOFTWARE CLOCK CALIBRATION
- AUTOMATIC POWER-FAIL DETECT AND SWITCH CIRCUITRY
- 56 BYTES OF GENERAL PURPOSE SRAM
- ULTRA-LOW BATTERY SUPPLY CURRENT OF 450nA
- AUTOMATIC LEAP YEAR COMPENSATION
- SPECIAL SOFTWARE PROGRAMMABLE OUTPUT
- TWO-WIRE I²C SERIAL INTERFACE SUPPORTS 100kHz PROTOCOL

Serial EEPROM Features

- 8192 BYTES OF GENERAL PURPOSE EEPROM (MORE THAN 1E6 ERASE/WRITE CYCLES)
- TWO-WIRE I²C SERIAL INTERFACE SUPPORTS 400kHz PROTOCOL
- BYTE AND PAGE WRITE (UP TO 32 BYTES)
- MORE THAN 40 YEAR DATA RETENTION
- SELF-TIMED PROGRAMMING CYCLE

Figure 1. Package

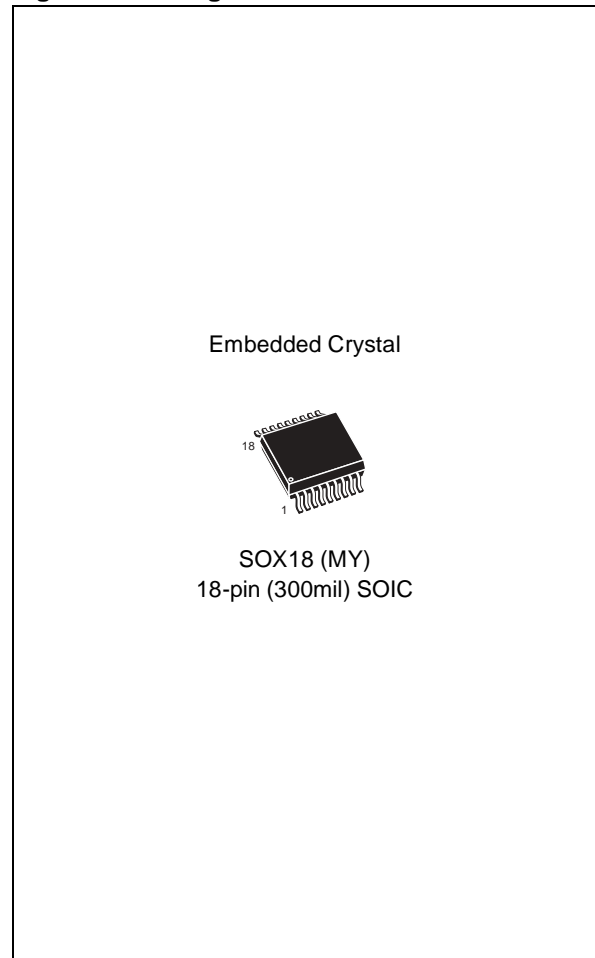


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SUMMARY DESCRIPTION

The M41T56C64 TIMEKEEPER® is a low power, 512-bit static CMOS RAM organized as 64 words by 8 bits plus a 64Kb EEPROM. A built-in 32,768 Hz oscillator (crystal controlled) and the first 8 bytes of the RAM are used for the clock/calendar function and are configured in binary coded decimal (BCD) format. Addresses and data are transferred serially via a two-line, bi-directional bus. The built-in address register is incremented automatically after each WRITE or READ data byte.

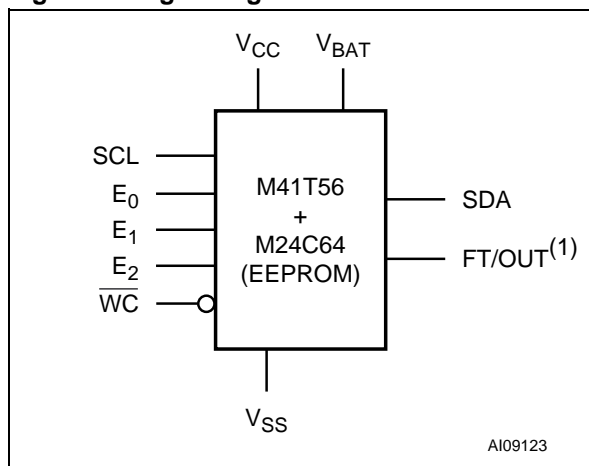
The M41T56C64 clock has a built-in power sense circuit which detects power failures and automatically switches to the battery supply during power failures. The energy needed to sustain the RAM and clock operations can be supplied from a small lithium coin cell.

Typical data retention time for the Serial RTC is in excess of 10 years with a 50mAh, 3V lithium cell. The M41T56C64 is supplied in an 18-lead Plastic SOIC package.

Calibration

As the crystal is molded together with the silicon in this package, ST can program the appropriate calibration value necessary to achieve ±6 ppm accuracy at 25°C after two reflows (see [Figure 4., page 4](#)). This calibration value will be written into address 1550h of the EEPROM. This clock accuracy can then be guaranteed to drift no more than ±4 ppm the first year, and ±2 ppm for each following year due to crystal aging.

Figure 2. Logic Diagram

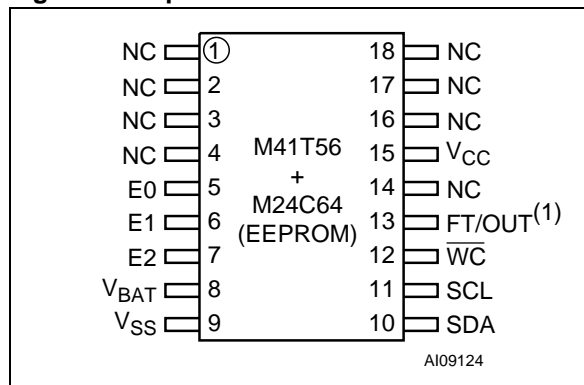


Note: 1. Open Drain output

Table 1. Signal Names

FT/OUT	Frequency Test / Output Driver (Open Drain)
SDA	Serial Data Address Input / Output
SCL	Serial Clock
WC	Write Control
E0, E1, E2	Chip Enables
V _{BAT}	Battery Supply Voltage
V _{CC}	Supply Voltage
V _{SS}	Ground

Figure 3. 18-pin SOIC Connections



Note: 1. Open Drain output

Figure 4. Crystal Accuracy Across Temperature

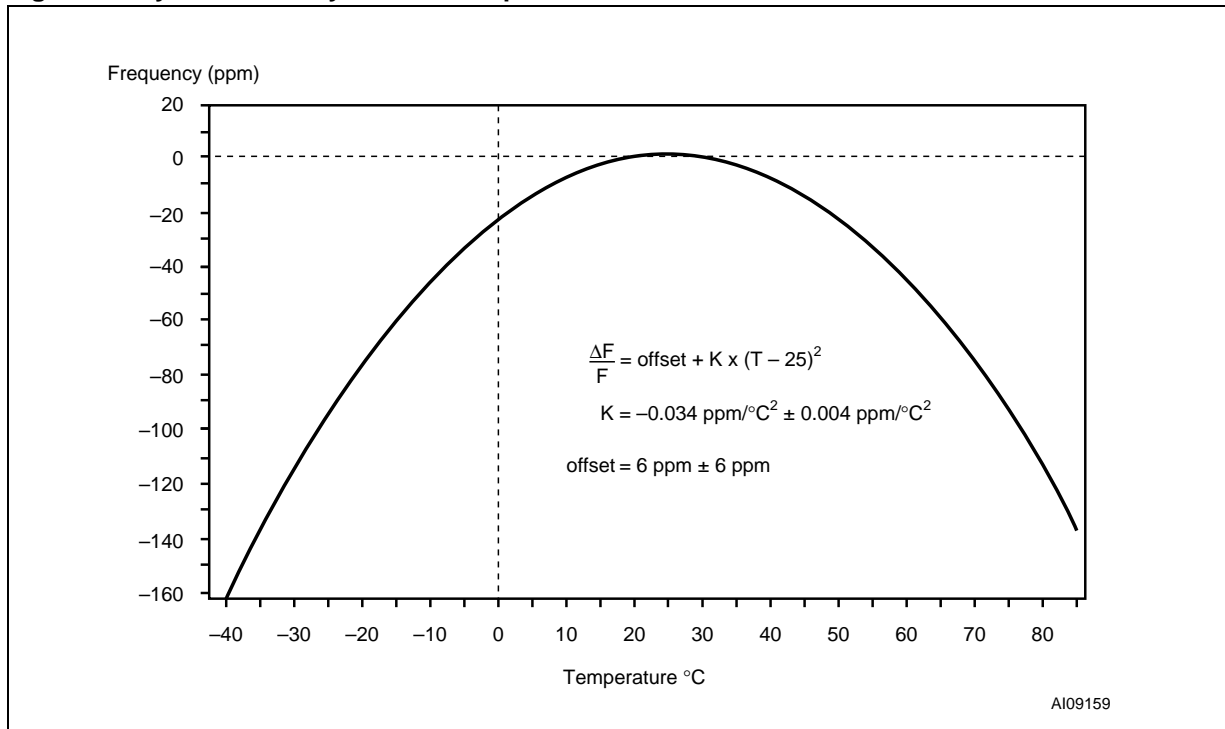


Figure 5. Block Diagram

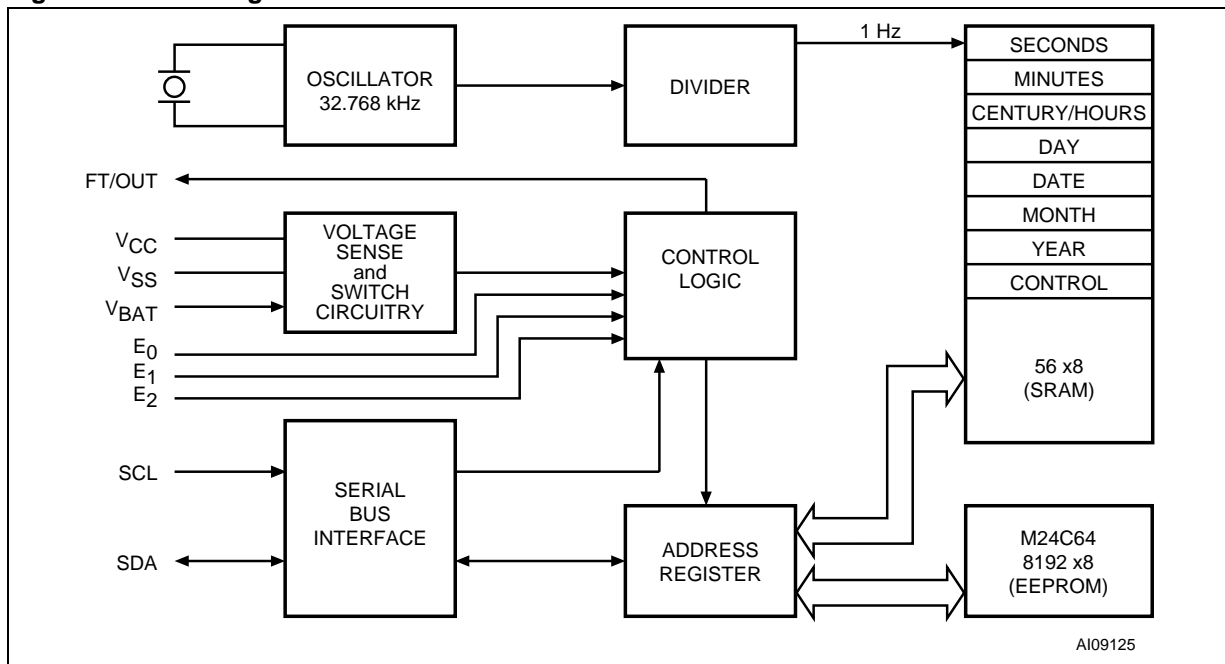


Table 2. Device Select Code

	Device Type Identifier ⁽¹⁾				Chip Enable Address ⁽²⁾			R \bar{W}
	b7	b6	b5	b4	b3	b2	b1	b0
M24C64	1	0	1	0	E2	E1	E0	R \bar{W}
M41T56	1	1	0	1	0	0	0	R \bar{W}

Note: 1. The most significant bit, b7, is sent first.

2. E0, E1, and E2 are compared against the respective external pins on the memory device.

OPERATION

Serial RTC Device

The M41T56C64 contains one Serial RTC (M41T56). For detailed information on how to use the devices, see the M41T56 datasheet, which is available from your local STMicroelectronics distributor or from the STMicroelectronics website, <http://www.st.com/rtc/>.

EEPROM Device

The M41T56C64 contains a 64 Kbit Serial EEPROM (M24C64). For detailed information on how to use the devices, see the M24C64 datasheet, which is available from your local STMicroelectronics distributor or from the STMicroelectronics website, <http://www.st.com/EEPROM/>.

MAXIMUM RATING

Stressing the device above the rating listed in the "Absolute Maximum Ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is

not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

Table 3. Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
T _A	Ambient Operating Temperature	-40 to 85	°C
T _{STG}	Storage Temperature (V _{CC} Off, Oscillator Off)	-55 to 125	°C
T _{SLD} ⁽¹⁾	Lead Solder Temperature for 10 seconds	240	°C
V _{IO}	Input or Output Voltages	-0.3 to 6.5	V
V _{CC}	Supply Voltage	-0.3 to 6.5	V
I _O	Output Current	20	mA
P _D	Power Dissipation	0.25	W

Note: 1. For SOX18 package, Lead-free (Pb-free) lead finish: Reflow at peak temperature of 240°C (total thermal budget not to exceed 180°C for between 90 to 150 seconds).

CAUTION: Negative undershoots below -0.3V are not allowed on any pin while in the Battery Back-up mode.

DC AND AC PARAMETERS

This section summarizes the operating and measurement conditions, as well as the DC and AC characteristics of the device. The parameters in the following DC and AC Characteristic tables are derived from tests performed under the Measure-

ment Conditions listed in the relevant tables. Designers should check that the operating conditions in their projects match the measurement conditions when using the quoted parameters.

Table 4. Operating and AC Measurement Conditions

Parameter	Value	Unit
Supply Voltage (V_{CC})	4.5 to 5.5	V
Ambient Operating Temperature (T_A)	-40 to 85	°C
Load Capacitance (C_L)	100	pF
Input Rise and Fall Times	50 (max)	ns
Input Pulse Voltages	$0.2V_{CC}$ to $0.8V_{CC}$	V
Input and Output Timing Ref. Voltages	$0.3V_{CC}$ to $0.7V_{CC}$	V

Note: Output Hi-Z is defined as the point where data is no longer driven.

Figure 6. AC Measurement I/O Waveform

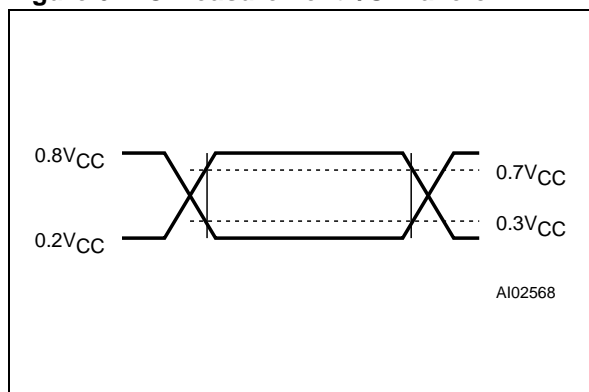


Table 5. Capacitance and Input Parameters

Symbol	Parameter ^(1,2)	Test Condition	Min	Max	Unit
C_{IN}	Input Capacitance (SCL)			13	pF
	Input Capacitance (SDA)			18	pF
	Input Capacitance (Other pins)			6	pF
Z_{WCL}	\overline{WC} Input Impedance	$V_{IN} < 0.5V$	5	20	kΩ
Z_{WCH}	\overline{WC} Input Impedance	$V_{IN} < 0.7V_{CC}$	500		kΩ
$C_{OUT}^{(3)}$	Output Capacitance (SDA)			18	pF
	Output Capacitance (FT/OUT)			10	pF

Note: 1. Effective capacitance measured with power supply at 5V; sampled, not 100% tested.
 2. At 25°C, $f = 400kHz$.
 3. Outputs deselected.

Table 6. DC Characteristics

Symbol	Parameter	Test Condition ⁽¹⁾	Min	Typ	Max	Unit
I _{LI}	Input Leakage Current	$0V \leq V_{IN} \leq V_{CC}$			±3	µA
I _{LO}	Output Leakage Current	$0V \leq V_{OUT} \leq V_{CC}$			±3	µA
I _{CC1}	Supply Current (Serial RTC Active)	Switch Frequency = 100kHz			310	µA
	Supply Current (Serial EEPROM Active)	$V_{CC} = 5V$, $f_c=400kHz$ (rise/fall time < 30ns)			2.2	mA
I _{CC2}	Supply Current (Standby)	SCL, SDA = $V_{CC} - 0.3V$		100		µA
V _{IL}	Input Low Voltage (SCL, SDA)		-0.3		1.5	V
	Input Low Voltage (E2, E1, E0)		-0.45		0.3V _{CC}	V
	Input Low Voltage (\overline{WC})		-0.45		0.5	V
V _{IH}	Input High Voltage (SCL, SDA)		3		V _{CC} + 0.8	V
	Input High Voltage (E2, E1, E1, \overline{WC})		0.7V _{CC}		V _{CC} + 1	V
V _{OL}	Output Low Voltage	I _{OL} = 3mA, V _{CC} = 5V			0.4	V
V _{BAT} ⁽²⁾	Battery Supply Voltage		2.5	3	3.5	V
I _{BAT}	Battery Supply Current	T _A = 25°C, V _{CC} = 0V, Oscillator ON, V _{BAT} = 3V		450	550	nA

Note: 1. Valid for Ambient Operating Temperature: T_A = -40 to 85°C; V_{CC} = 4.5 to 5.5V (except where noted).

2. STMicroelectronics recommends the RAYOVAC BR1225 or BR1632 (or equivalent) as the battery supply.

Figure 7. Bus Timing Requirements Sequence (Serial RTC)

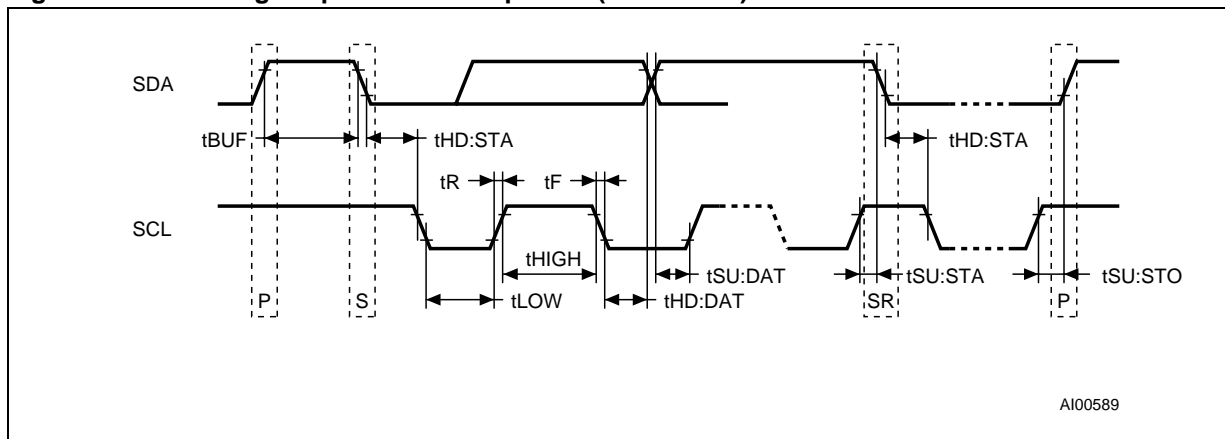


Table 7. AC Characteristics, (Serial RTC, M41T56)

Symbol	Parameter ⁽¹⁾	Min	Max	Unit
f _{SCL}	SCL Clock Frequency	0	100	kHz
t _{LOW}	Clock Low Period	4.7		μs
t _{HIGH}	Clock High Period	4		μs
t _R	SDA and SCL Rise Time		1	μs
t _F	SDA and SCL Fall Time		300	ns
t _{HD:STA}	START Condition Hold Time (after this period the first clock pulse is generated)	4		μs
t _{SU:STA}	START Condition Setup Time (only relevant for a repeated start condition)	4.7		μs
t _{SU:DAT}	Data Setup Time	250		ns
t _{HD:DAT} ⁽²⁾	Data Hold Time	0		μs
t _{SU:STO}	STOP Condition Setup Time	4.7		μs
t _{BUF}	Time the bus must be free before a new transmission can start	4.7		μs
t _{LP}	Low-pass filter input time constant (SDA and SCL) for Serial RTC	0.25	1	μs

Note: 1. Valid for Ambient Operating Temperature: T_A = -40 to 85°C; V_{CC} = 4.5 to 5.5V (except where noted).
 2. Transmitter must internally provide a hold time to bridge the undefined region (300ns max.) of the falling edge of SCL.

Figure 8. AC Waveforms (Serial EEPROM)

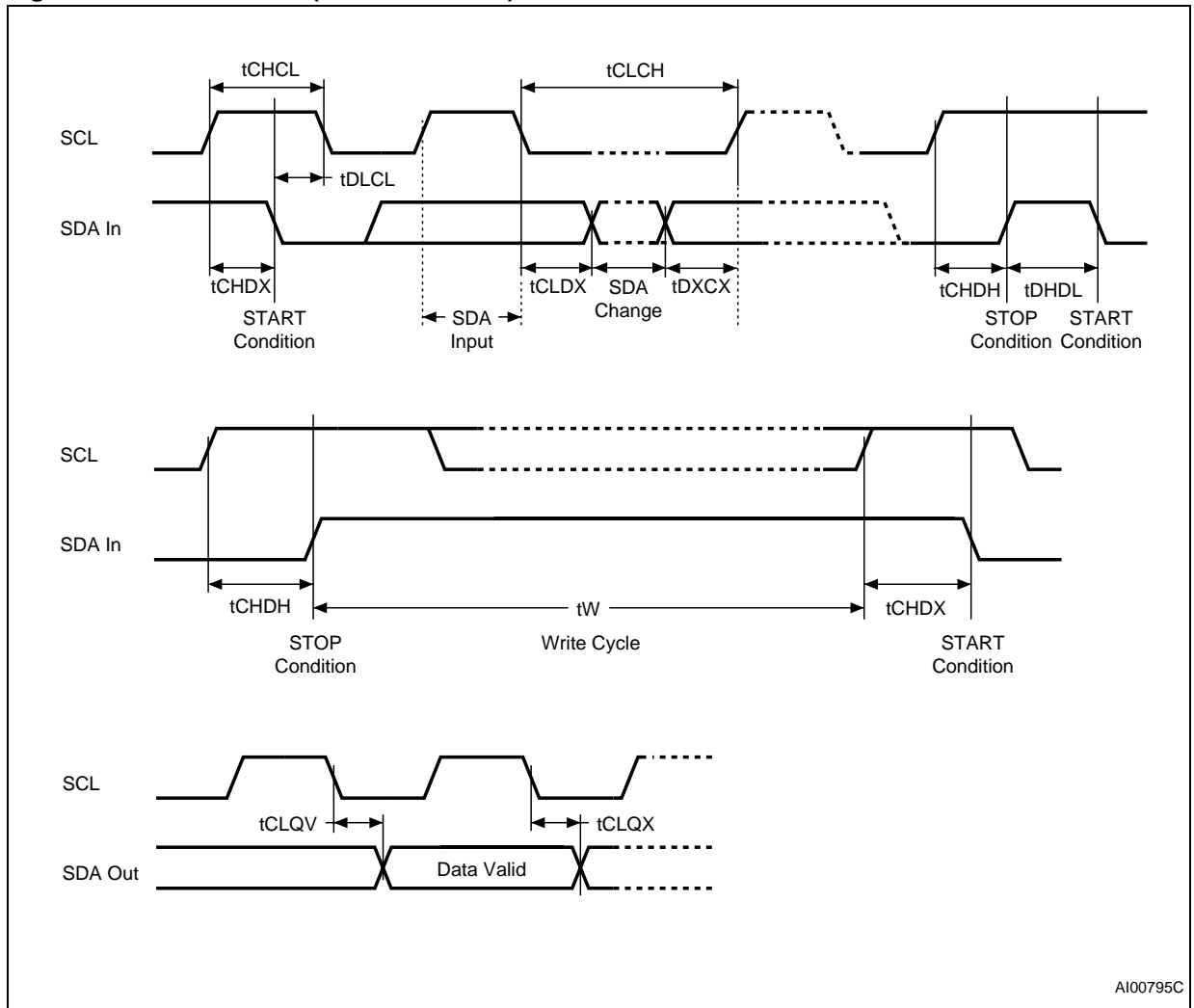


Table 8. AC Characteristics (Serial EEPROM, M24C64)

Symbol	Alt.	Parameter	Test Condition	Min.	Max.	Unit
f_C	f_{SCL}	Clock Frequency			400	kHz
t_{CHCL}	t_{HIGH}	Clock Pulse Width High		600		ns
t_{CLCH}	t_{LOW}	Clock Pulse Width Low		1300		ns
$t_{DL1DL2}^{(2)}$	t_F	SDA Fall Time		20	300	ns
t_{DXCX}	$t_{SU:DAT}$	Data In Set Up Time		100		ns
t_{CLDX}	$t_{HD:DAT}$	Data In Hold Time		0		ns
t_{CLQX}	t_{DH}	Data Out Hold Time		200		ns
$t_{CLQV}^{(3)}$	t_{AA}	Clock Low to Next Data Valid (Access Time)		200	900	ns
$t_{CHDX}^{(1)}$	$t_{SU:STA}$	Start Condition Set Up Time		600		ns
t_{DLCL}	$t_{HD:STA}$	Start Condition Hold Time		600		ns
t_{CHDH}	$t_{SU:STO}$	Stop Condition Set Up Time		600		ns
t_{DHDL}	t_{BUF}	Time between Stop Condition and Next Start Condition		1300		ns
t_W	t_{WR}	Write Time			5 or ⁽⁴⁾ 10	ms
t_{NS}		Pulse Width Ignored (Input Filter on SCL and SDA for Serial EEPROM)	Single glitch		100	ns

Note: 1. For a reSTART condition, or following a Write cycle.

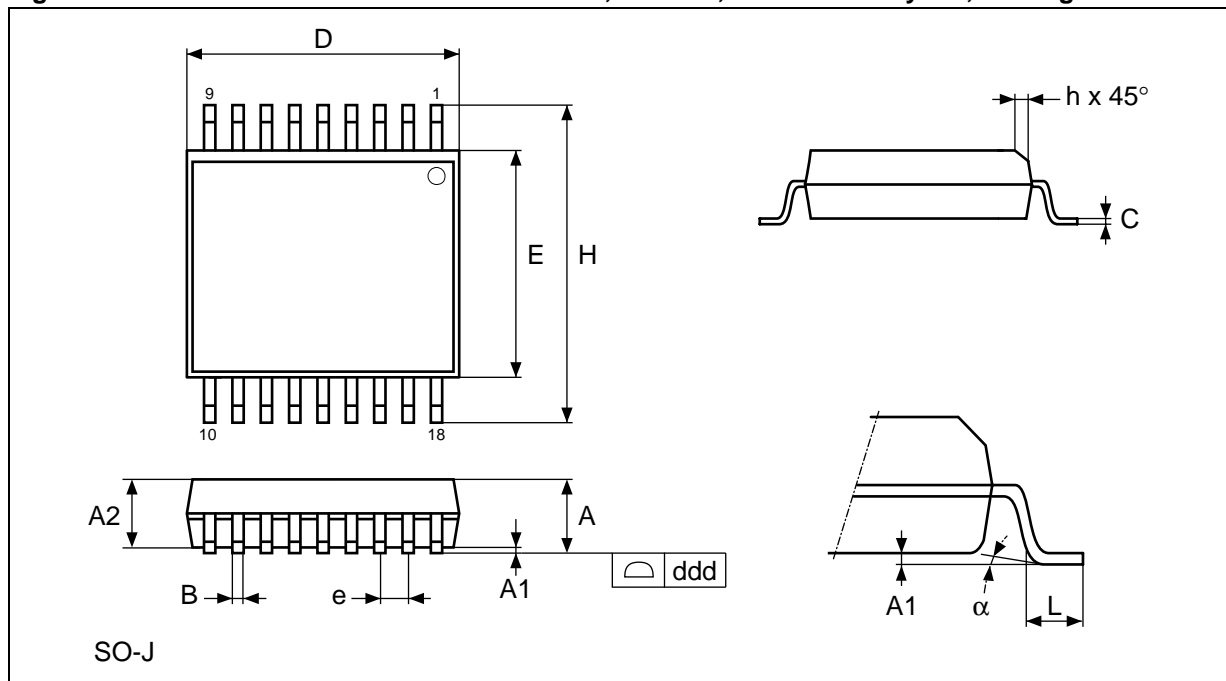
2. Sampled only, not 100% tested.

3. To avoid spurious START and STOP conditions, a minimum delay is placed between SCL=1 and the falling or rising edge of SDA.

4. The Write Time of 5 ms only applies to devices bearing the process letter "B" in the package marking (on the top side of the package), otherwise (for devices bearing the process letter "N") the Write Time is 10 ms. For further details, please contact your nearest ST sales office, and ask for a copy of the Product Change Notice PCEE0036.

PACKAGE MECHANICAL

Figure 9. SOX18 – 18-lead Plastic Small Outline, 300mils, Embedded Crystal, Package Outline



Note: Drawing is not to scale.

Table 9. SOX18 – 18-lead Plastic Small Outline, 300mils, Embedded Crystal, Package Mech.

Symbol	millimeters			inches		
	Typ	Min	Max	Typ	Min	Max
A		2.44	2.69		0.096	0.106
A1		0.15	0.31		0.006	0.012
A2		2.29	2.39		0.090	0.094
B		0.41	0.51		0.016	0.020
C		0.20	0.31		0.008	0.012
D	11.61	11.56	11.66	0.457	0.455	0.459
ddd			0.10			0.004
E		7.57	7.67		0.298	0.302
e	1.27	–	–	0.050	–	–
H		10.16	10.52		0.400	0.414
L		0.51	0.81		0.020	0.032
α		0°	8°		0°	8°
N		18			18	

PART NUMBERING

Table 10. Ordering Information Scheme

Example:	M41T	56C64	MY	6	TR
Device Type	M41T				
Supply Voltage and Write Protect Voltage	56C64 = V_{CC} = 4.5 to 5.5V				
Package	MY ⁽¹⁾ = SOX18				
Temperature Range	6 = -40°C to 85°C				
Shipping Method	blank = Tubes TR = Tape & Reel				

Note: 1. The SOX18 package includes an embedded 32,768Hz crystal.

For other options, or for more information on any aspect of this device, please contact the ST Sales Office nearest you.

REVISION HISTORY

Table 11. Document Revision History

Date	Version	Description
14-Sep-04	1.0	First Edition

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